

IN THE SPECIFICATION

Please replace the paragraph beginning at page 1, line 25, with the following rewritten paragraph:

--A dispersion slurry of fumed silica or colloidal silica has been used in a chemical mechanical polishing (CMP), (Japanese Patent Laid Open No. JP62-30333A ~~30333-1987~~, JP5-154760A ~~154760-1993~~, JP2001-342455A ~~342455-2001~~). Generally, a polishing process of a silicon wafer is classified into three processes, i.e., a primary polishing, a secondary polishing and a finishing polishing. It is required that after the finishing polishing the final surface has no scratch and haze. Furthermore, a high purity of the polishing slurry is strongly required in order to prevent metal ionic contaminations resulting from taking metal ions, especially sodium, into the surface layer of the substrate at the time of polishing.--

Please replace the paragraph beginning at page 6, line 25, with the following rewritten paragraph:

--A silica powder having low impurities concentrations as described above and a particle size as described above is, for example, a fumed silica or the like produced by a dry process, such as a flame hydrolysis method or the like. If the silica powder is produced by a wet process, it is difficult to obtain a slurry having the above mentioned levels of impurities concentrations or less. As the silica powder produced by a dry process it is preferable to use, for example, the silica powder produced by the method described in Japanese Patent Laid Open No. JP2002-3213A ~~3213-2002~~. This production method is to produce an amorphous fine silica powder by introducing a gaseous silicon compound into a flame and hydrolyzing it. In this production method, the amorphous silica powder having an average particle size (median size) of from 0.08 to 0.8 μ m and a specific surface area of from 5 to 30 m²/g as measured by the BET method, is produced by making the flame temperature to be a melting point of silica, growing the silica particle while keeping the silica concentration in the flame

of more than 0.25 kg / Nm^3 , and maintaining the grown silica particle at a high temperature of more than the melting point for a short time.--